

N-Channel Enhancement Mode MOSFET

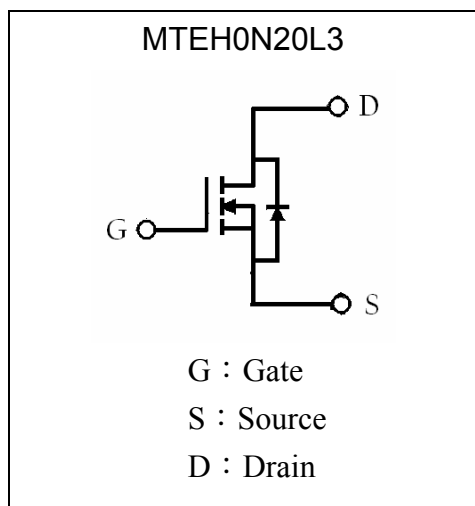
MTEH0N20L3

BV_{DSS}	200V
I_D	1A
$R_{DS(on)}@V_{GS}=10V, I_D=0.5A$	$0.98\ \Omega$ (typ)
$R_{DS(on)}@V_{GS}=5V, I_D=0.1A$	$0.97\ \Omega$ (typ)

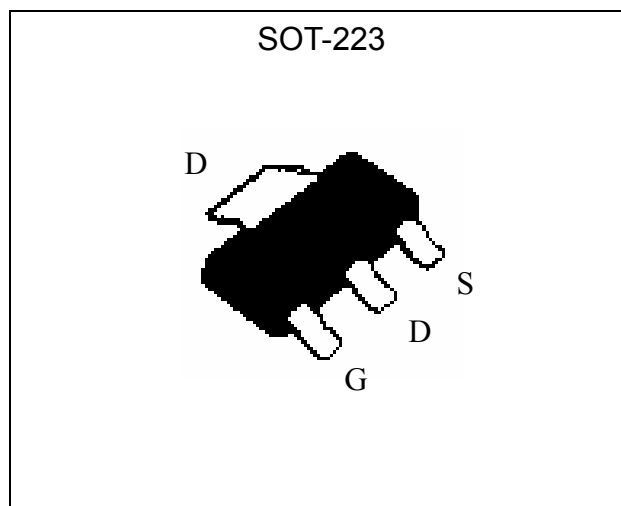
Features

- Single Drive Requirement
- Low On-resistance
- Fast Switching Characteristic
- Pb-free lead plating and halogen-free package

Symbol



Outline



Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V_{DS}	200	V
Gate-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current @ $V_{GS}=10V, T_A=25^\circ C$	I_D	1	A
Continuous Drain Current @ $V_{GS}=10V, T_A=70^\circ C$	I_D	0.8	A
Pulsed Drain Current *1	I_{DM}	4	A
Single Pulse Avalanche Energy @ $L=10mH, I_D=1A, V_{DD}=50V$	E_{AS}	5	mJ
Total Power Dissipation *2	P_D	$T_A=25^\circ C$	W
		$T_A=70^\circ C$	
Operating Junction and Storage Temperature Range	T_j, T_{stg}	-55~+150	°C

Note : *1. Pulse width limited by safe operating area

*2. Surface mounted on a 1 in² pad of 2 oz. copper, t≤10s.

**Thermal Data**

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	$R_{th,j-c}$	25	$^{\circ}\text{C/W}$
Thermal Resistance, Junction-to-ambient, max	$R_{th,j-a}$	50 (Note)	$^{\circ}\text{C/W}$

Note : Surface mounted on a 1 in² pad of 2 oz. copper, $\leq 10\text{s}$; 120°C/W when mounted on minimum copper pad.

Electrical Characteristics ($T_j=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	200	-	-	V	V _{GS} =0V, I _D =250μA
V _{GS(th)}	2	2.9	4		V _{DS} =V _{GS} , I _D =250μA
I _{GSS}	-	-	±100	nA	V _{GS} =±30V, V _{DS} =0V
I _{DSS}	-	-	10	μA	V _{DS} =200V, V _{GS} =0V
	-	-	250		V _{DS} =160V, V _{GS} =0V, T _j =70°C
*R _{DS(ON)}	-	0.98	1.1	Ω	V _{GS} =10V, I _D =0.5A
	-	0.97	1.3		V _{GS} =5V, I _D =0.1A
*G _{FS}	-	1.9	-	S	V _{DS} =5V, I _D =0.5A
Dynamic					
C _{iss}	-	137	-	pF	V _{DS} =25V, V _{GS} =0V, f=1MHz
C _{oss}	-	15	-		
C _{rss}	-	6	-		
*t _{d(ON)}	-	33	-	ns	V _{DS} =100V, I _D =1A, V _{GS} =10V, R _G =25Ω
*t _r	-	50	-		
*t _{d(OFF)}	-	150	-		
*t _f	-	75	-		
*Q _g	-	5.8	-	nC	V _{DS} =160V, I _D =1A, V _{GS} =10V
*Q _{gs}	-	0.7	-		
*Q _{gd}	-	2.5	-		
Source-Drain Diode					
*I _S	-	-	1	A	
*I _{SM}	-	-	4		
*V _{SD}	-	-	1.2	V	V _{GS} =0V, I _S =1A
*t _{rr}	-	90	-	ns	V _{GS} =0V, I _F =1A, dI/dt=100A/μs
*Q _{rr}	-	280	-	nC	

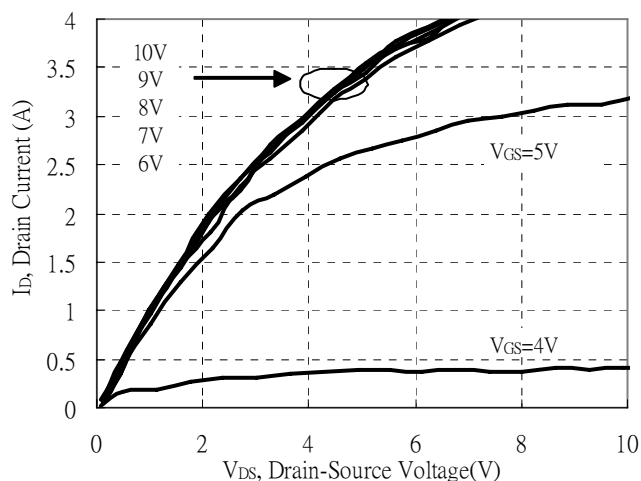
*Pulse Test : Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

Ordering Information

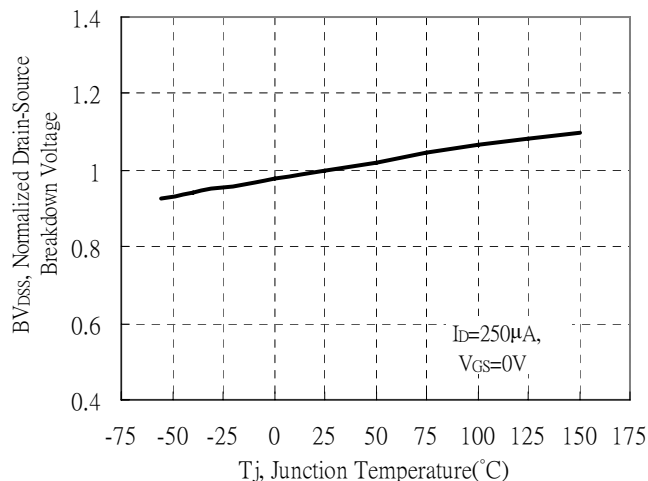
Device	Package	Shipping
MTEH0N20L3-0-T3-G	SOT-223 (Pb-free lead plating and halogen-free package)	2500 pcs / Tape & Reel

Typical Characteristics

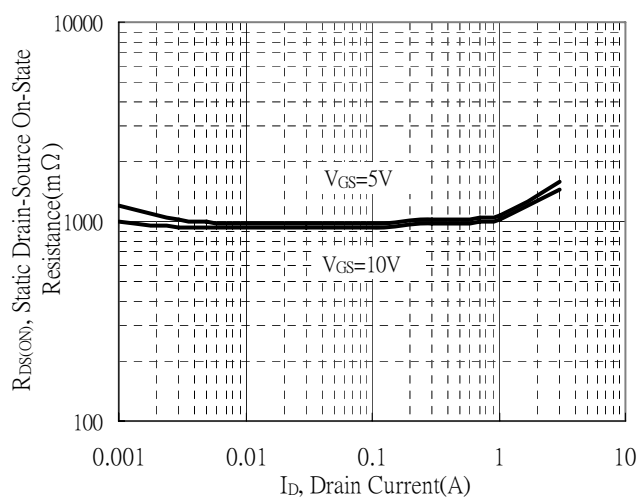
Typical Output Characteristics



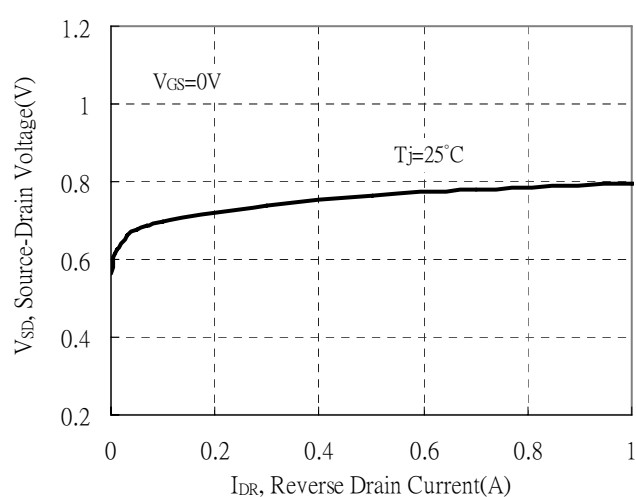
Breakdown Voltage vs Ambient Temperature



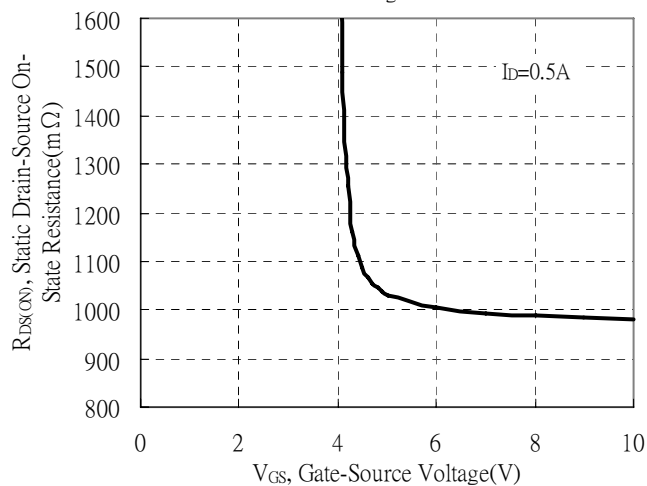
Static Drain-Source On-State resistance vs Drain Current



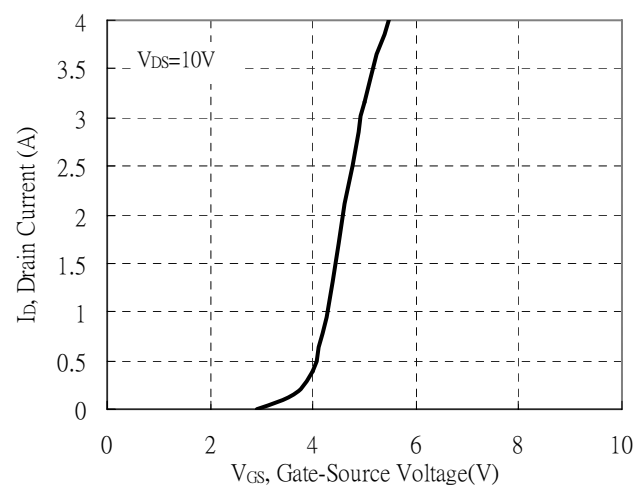
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

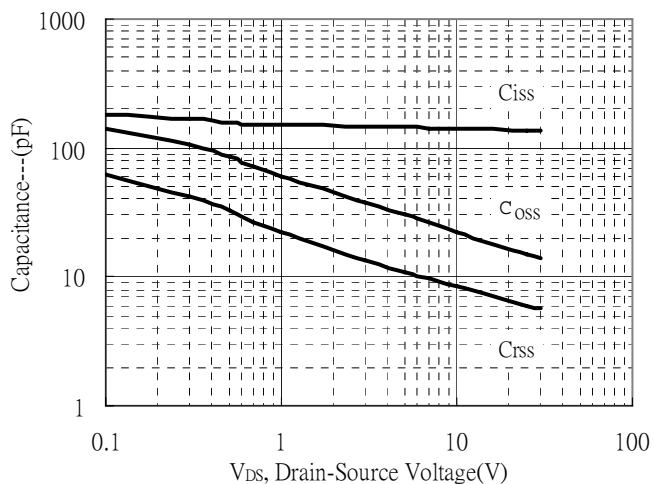


Typical Transfer Characteristics

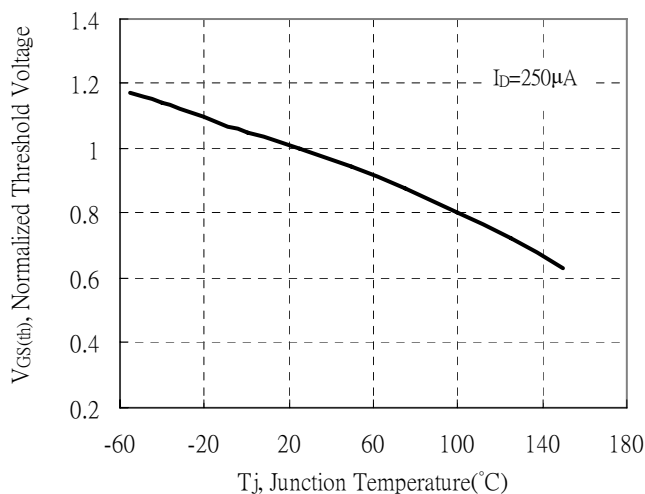


Typical Characteristics(Cont.)

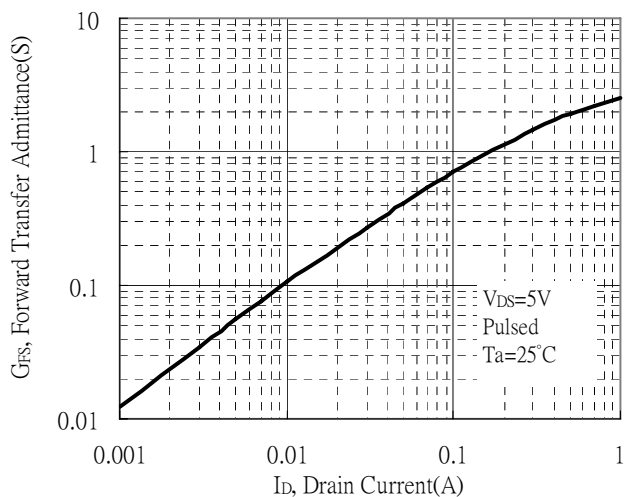
Capacitance vs Drain-to-Source Voltage



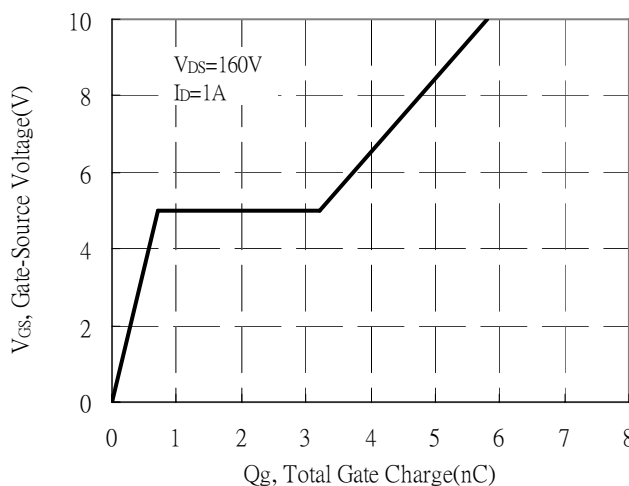
Threshold Voltage vs Junction Temperature



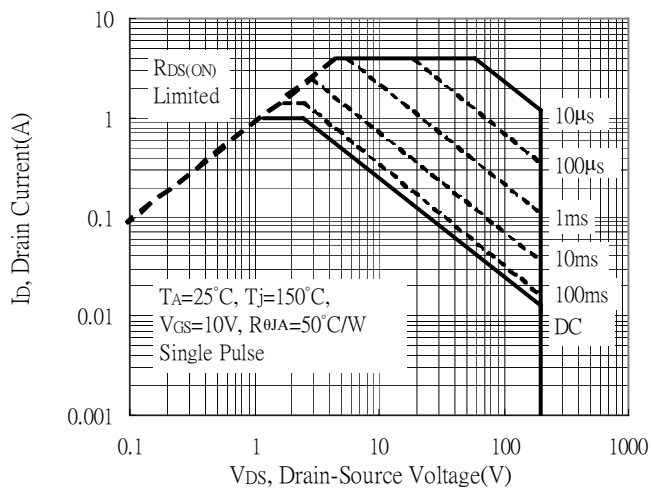
Forward Transfer Admittance vs Drain Current



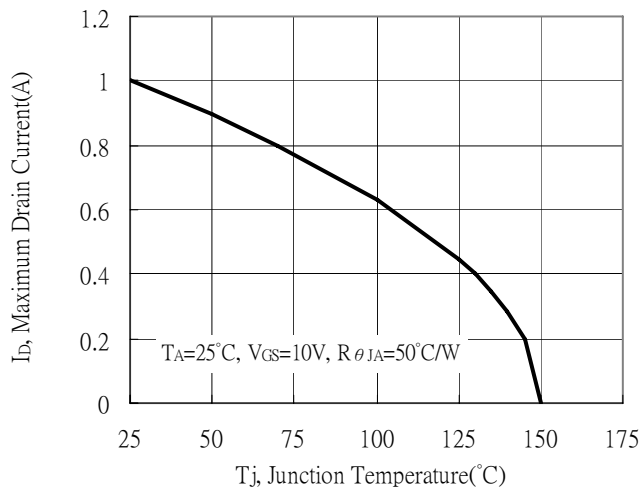
Gate Charge Characteristics



Maximum Safe Operating Area

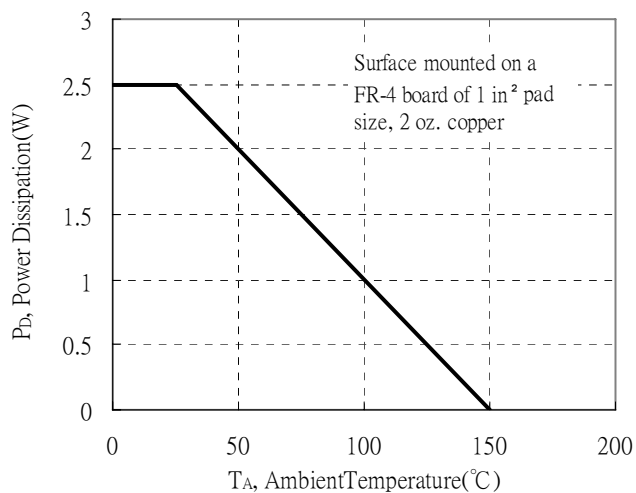


Maximum Drain Current vs Junction Temperature

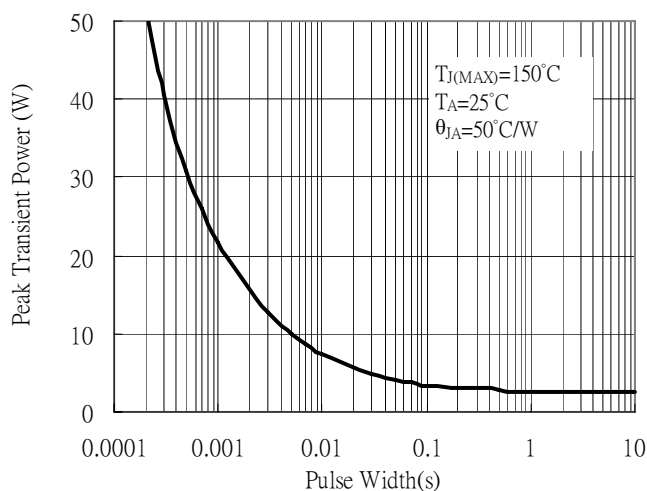


Typical Characteristics(Cont.)

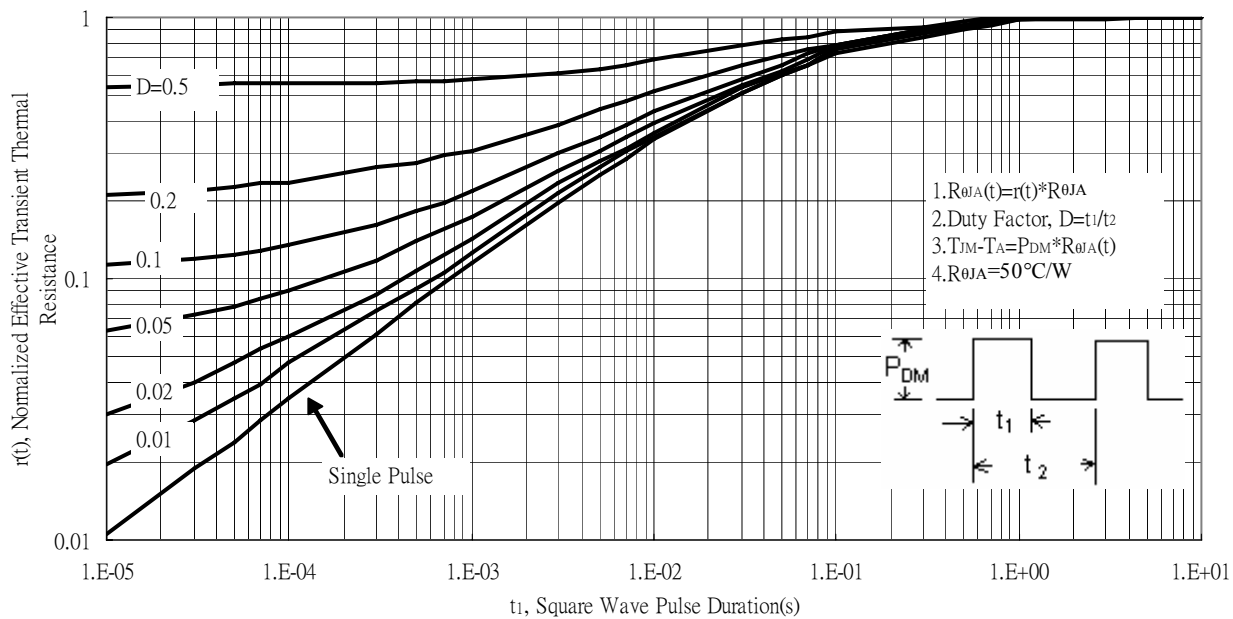
Power Derating Curve



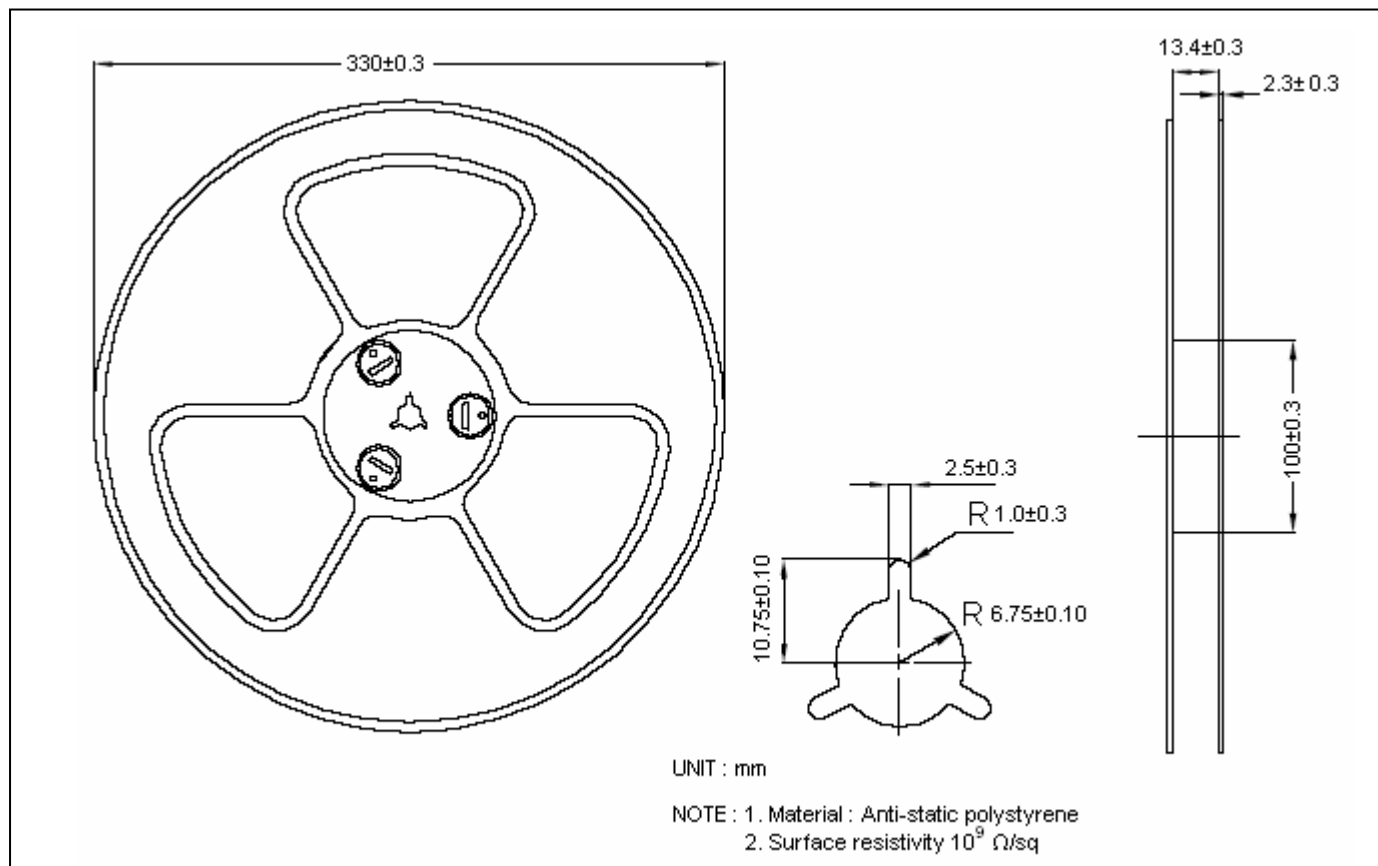
Single Pulse Maximum Power Dissipation



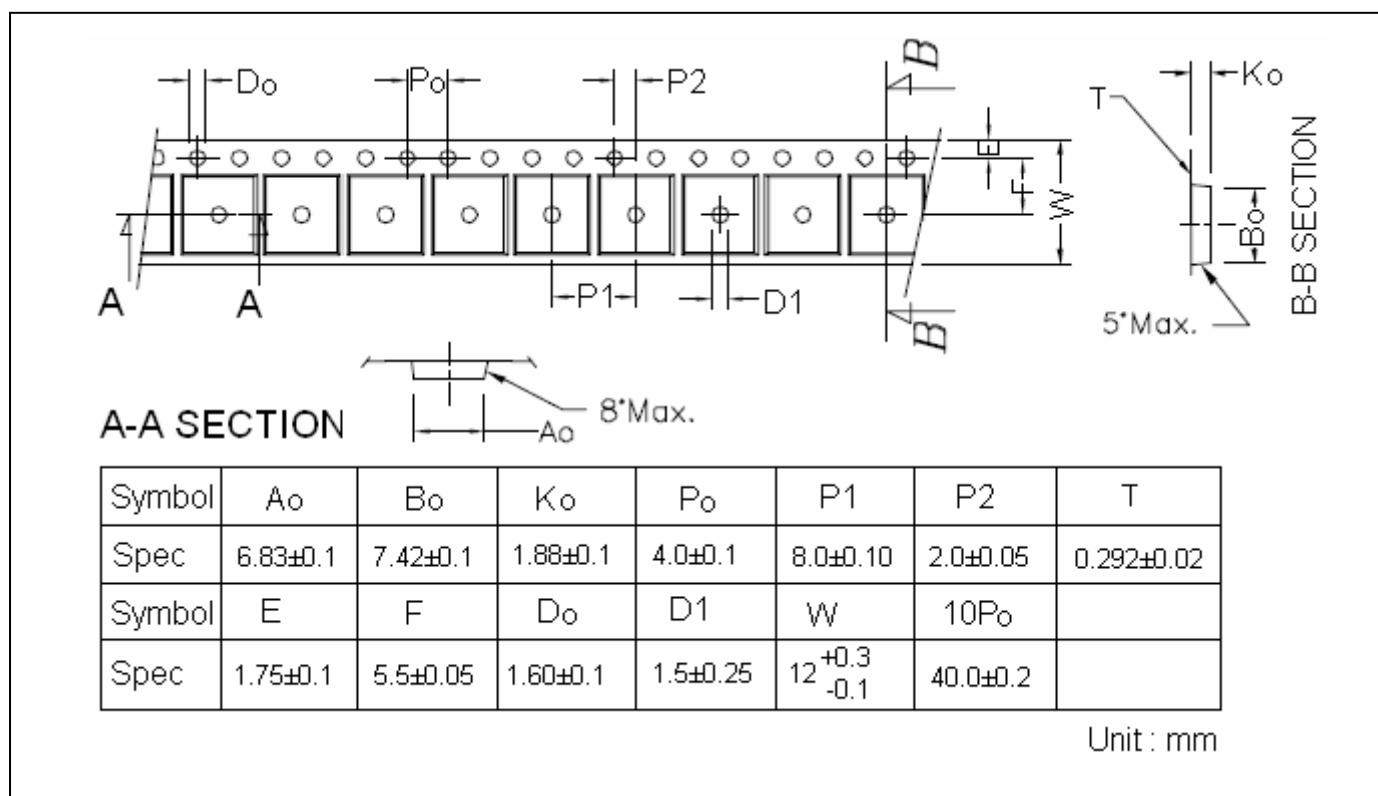
Transient Thermal Response Curves



Reel Dimension



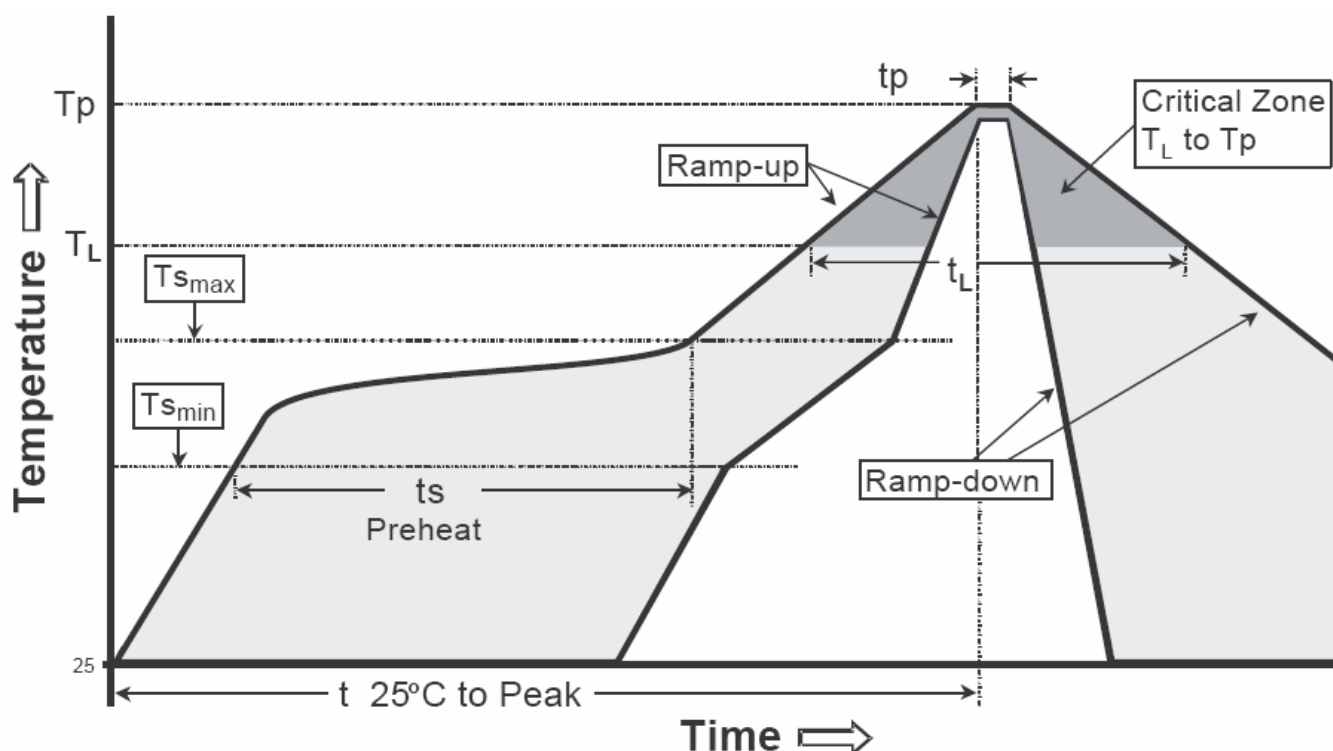
Carrier Tape Dimension



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

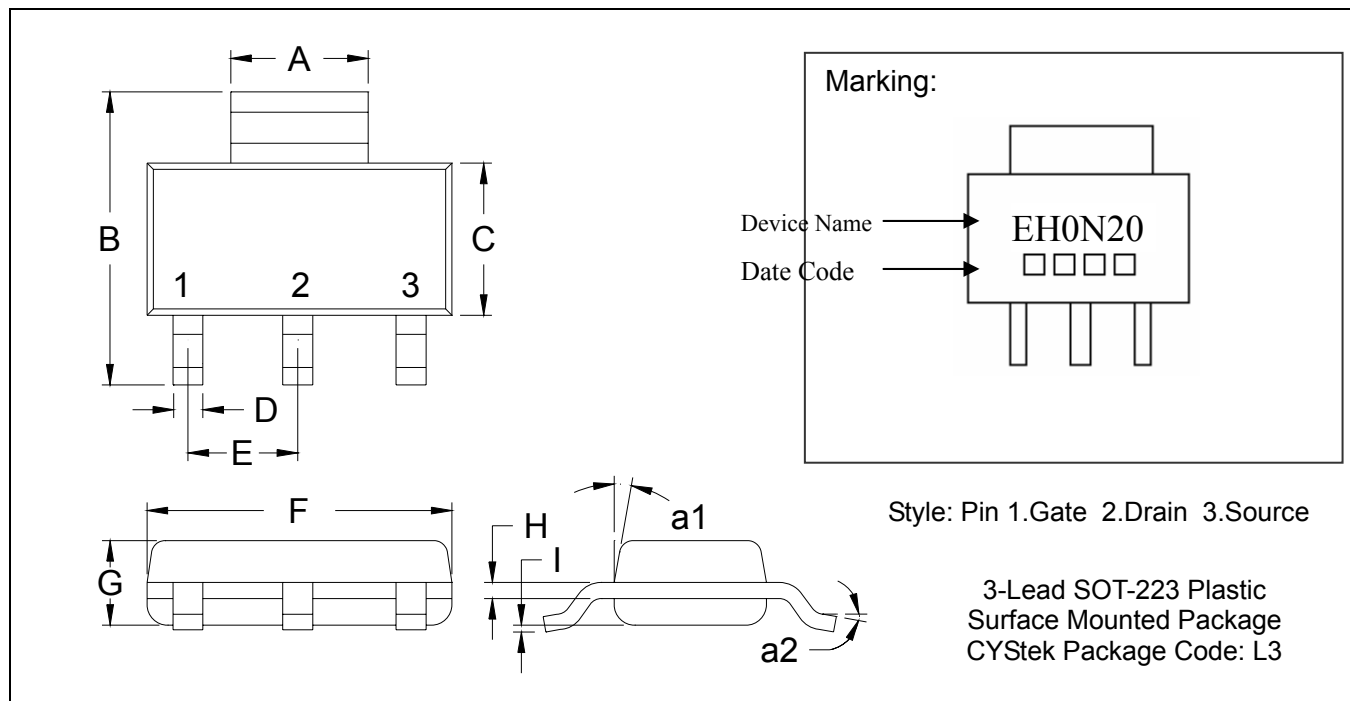
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T _{s min})	100°C	150°C
-Temperature Max(T _{s max})	150°C	200°C
-Time(t _{s min} to t _{s max})	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _p)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

SOT-223 Dimension



*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1142	0.1220	2.90	3.10	G	0.0551	0.0709	1.40	1.80
B	0.2638	0.2874	6.70	7.30	H	0.0098	0.0138	0.25	0.35
C	0.1299	0.1457	3.30	3.70	I	0.0008	0.0039	0.02	0.10
D	0.0236	0.0315	0.60	0.80	a1	*13°	-	*13°	-
E	*0.0906	-	*2.30	-	a2	0°	10°	0°	10°
F	0.2480	0.2638	6.30	6.70					

Notes: 1.Controlling dimension: millimeters.

2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.

3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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